Regulator Family, 400 mA, 2% and 4% Voltage

Description

The NCV4274 and NCV4274A is a precision micro-power voltage regulator with an output current capability of 400 mA available in the DPAK, D2PAK and SOT-223 packages.

The output voltage is accurate within $\pm 2.0\%$ or $\pm 4.0\%$ depending on the version with a maximum dropout voltage of 0.5 V with an input up to 40 V. Low quiescent current is a feature drawing only 150 μ A with a 1 mA load. This part is ideal for automotive and all battery operated microprocessor equipment.

The regulator is protected against reverse battery, short circuit, and thermal overload conditions. The device can withstand load dump transients making it suitable for use in automotive environments.

Features

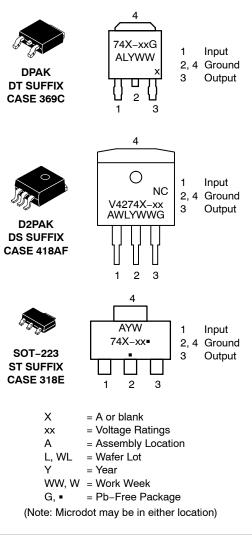
- 2.5, 3.3 V, 5.0 V, 8.5 V, ±2.0% Output Options
- 2.5, 3.3 V, 5.0 V, ±4.0% Output Options
- Low 150 µA Quiescent Current at 1 mA load current
- 400 mA Output Current Capability
- Fault Protection
- +60 V Peak Transient Voltage with Respect to GND
 - -42 V Reverse Voltage
 - Short Circuit
 - Thermal Overload
- Very Low Dropout Voltage
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q100 Qualified and PPAP Capable
- These are Pb–Free Devices



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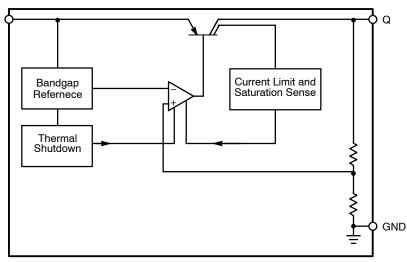
www.onsemi.com

MARKING DIAGRAMS



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 15 of this data sheet.





Pin Definitions and Functions

I

Pin No.	Symbol	Function
1	I	Input; Bypass directly at the IC a ceramic capacitor to GND.
2,4	GND	Ground
3	Q	Output; Bypass with a capacitor to GND.

1. DPAK 3LD package code 6025

2. D2PAK 3LD package code 6083

ABSOLUTE MAXIMUM RATINGS

Pin Symbol, Parameter		Symbol	Condition	Min	Max	Unit
I, Input-to-Regulator	Voltage	VI		-42	45	V
	Current	I _I		Internally Limited	Internally Limited	
I, Input peak Transient Voltage to Regulator with Respect to GND		VI			60	V
Q , Regulated Output	Voltage	V _Q	$V_Q = V_I$	-1.0	40	V
	Current	Ι _Q		Internally Limited	Internally Limited	
GND, Ground Current		I _{GND}		-	100	mA
Junction Temperature Storage Temperature		T _J T _{Stg}		_ _50	150 150	°C °C
ESD Capability, Human Body Model		ESD _{HB}		4		kV
ESD Capability, Machine Model		ESD _{MM}		200		V
ESD Capability, Charged Device Model		ESD _{CDM}		1		kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.This device series incorporates ESD protection and is tested by the following methods:

ESD HBM tested per AEC-Q100-002 (EIA/JESD22-A114)

ESD MM tested per AEC-Q100-003 (EIA/JESD22-A115)

ESD CDM tested per EIA/JES D22/C101, Field Induced Charge Model

OPERATING RANGE

Parameter	Symbol	Condition	Min	Max	Unit
Input Voltage (8.5 V Version)	VI		9.0	40	V
Input Voltage (5.0 V Version)	VI		5.5	40	V
Input Voltage (3.3 V, and 2.5 V Version)	VI		4.5	40	V
Junction Temperature	TJ		-40	150	°C

THERMAL RESISTANCE

Parameter	Symbol	Condition	Min	Мах	Unit	
Junction-to-Ambient	DPAK	R _{thja}		-	70 (Note 4)	°C/W
Junction-to-Ambient	D2PAK	R _{thja}		-	60 (Note 4)	°C/W
Junction-to-Case	DPAK	R _{thjc}		-	4	°C/W
Junction-to-Case	D2PAK	R _{thjc}		-	3	°C/W
Junction-to-Tab	SOT-223	Ψ–JLX, ΨLX		-	14.5 (Note 5)	°C/W
Junction-to-Ambient	SOT-223	$R_{\theta JA}, \theta_{JA}$		-	169.7 (Note 5)	°C/W

Soldered in, minimal footprint, FR4
 1 oz copper, 5 mm² copper area, FR4

LEAD FREE SOLDERING TEMPERATURE AND MSL

Parameter		mbol	Condition	Min	Мах	Unit
Lead Free Soldering, (Note 6) Reflow (SMD styles only), Pb-	T Free	T _{sld}	60s – 150s Above 217s 40s Max at Peak	_	265 pk	°C
Moisture Sensitivity Level	N	/ISL	DPAK and D2PAK SOT-223	1 3	-	

6. Per IPC/JEDEC J-STD-020C

ELECTRICAL CHARACTERISTICS

 $-40^\circ C < T_J < 150^\circ C; \, V_I$ = 13.5 V unless otherwise noted.

			Min	Тур	Max	Min	Тур	Max	
Parameter	Symbol	Test Conditions	N	CV427	4A	1	NCV42	74	Unit
REGULATOR			•						4
Output Voltage (8.5 V Version)	V _Q	5 mA < I _Q < 200 mA 9.5 V < V _I < 40 V	8.33	8.5	8.67	-	-	-	V
Output Voltage (8.5 V Version)	V _Q	5 mA < I _Q < 400 mA 9.5 V < V _I < 28 V	8.33	8.5	8.67	-	-	_	V
Output Voltage (5.0 V Version)	V _Q	5 mA < I _Q < 400 mA 6 V < V _I < 28 V	4.9	5.0	5.1	4.8	5.0	5.2	V
Output Voltage (5.0 V Version)	V _Q	5 mA < I _Q < 200 mA 6 V < V _I < 40 V	4.9	5.0	5.1	4.8	5.0	5.2	V
Output Voltage (3.3 V Version)	V _Q	5 mA < I _Q < 400 mA 4.5 V < V _I < 28 V	3.23	3.3	3.37	3.17	3.3	3.43	V
Output Voltage (3.3 V Version)	V _Q	5 mA < I _Q < 200 mA 4.5 V < V _I < 40 V	3.23	3.3	3.37	3.17	3.3	3.43	V
Output Voltage (2.5 V Version)	V _Q	5 mA < I _Q < 400 mA 4.5 V < V _I < 28 V	2.45	2.5	2.55	2.4	2.5	2.6	V
Output Voltage (2.5 V Version)	V _Q	5 mA < I _Q < 200 mA 4.5 V < V _I < 40 V	2.45	2.5	2.55	2.4	2.5	2.6	V
Current Limit	Ι _Q	-	400	600	_	400	600	_	mA
Quiescent Current	I _q	$I_{Q} = 1 \text{ mA}$ $V_{Q} = 8.5 \text{ V}$ $V_{Q} = 5.0 \text{ V}$ $V_{Q} = 2.5 \text{ V}$ $I_{Q} = 250 \text{ mA}$ $V_{Q} = 8.5 \text{ V}$ $V_{Q} = 5.0 \text{ V}$ $V_{Q} = 3.3 \text{ V}$ $V_{Q} = 2.5 \text{ V}$ $I_{Q} = 400 \text{ mA}$ $V_{Q} = 8.5 \text{ V}$ $V_{Q} = 5.0 \text{ V}$ $V_{Q} = 3.3 \text{ V}$ $V_{Q} = 2.5 \text{ V}$	- - - - - - - - - - - -	195 190 145 140 10 13 12 20 20 30 28	250 250 250 250 15 15 20 20 35 35 45 45	- - - - - - - - - -	- 190 145 140 - 10 13 12 - 20 30 28	- 250 250 250 - 15 20 20 - 35 45 45	μΑ μΑ μΑ mA mA mA mA mA mA mA
Dropout Voltage 8.5 V Version 5.0 V Version 3.3 V Version 2.5 V Version	V _{DR}	$ \begin{split} I_Q &= 250 \text{ mA}, \\ V_{DR} &= V_I - V_Q \\ V_I &= 8.5 \text{ V} \\ V_I &= 5.0 \text{ V} \\ V_I &= 4.5 \text{ V} \\ V_I &= 4.5 \text{ V} \end{split} $		250 250 - -	500 500 1.27 2.05	- - -	_ 250 _ _	_ 500 1.33 2.1	mV mV V V
Load Regulation	ΔV_Q	$I_Q = 5 \text{ mA to } 400 \text{ mA}$	-	7	20	-	7	30	mV
Line Regulation	ΔV_Q	$\Delta V_{I} = 12 \text{ V to } 32 \text{ V}$ I _Q = 5 mA	-	10	25	-	10	25	mV
Power Supply Ripple Rejection	P _{SRR}	fr = 100 Hz, V _r = 0.5 V _{PP}	-	60	-	-	60	_	dB
Temperature output voltage drift	$\Delta V_Q / \Delta T$		-	0.5	-	-	0.5	-	mV/K
Thermal Shutdown Temperature*	T _{SD}	I _O = 5 mA	165	-	210	165	-	210	°C

*Guaranteed by design, not tested in production

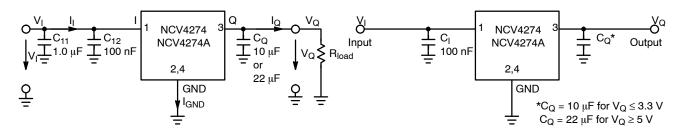
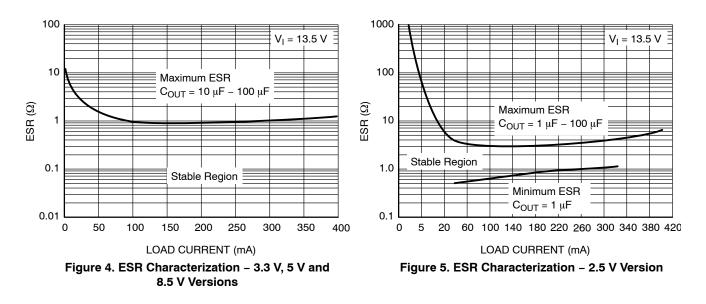


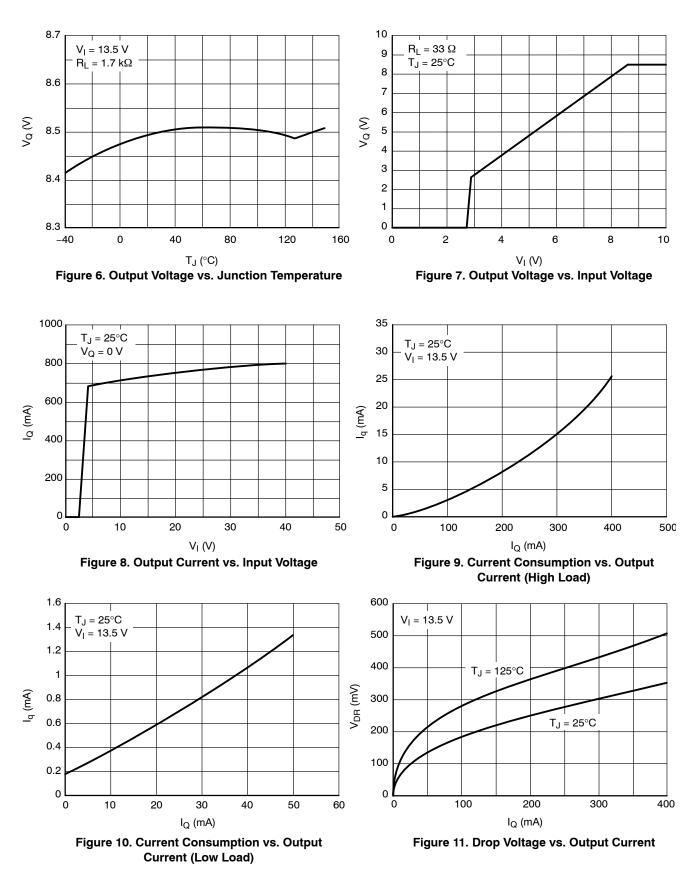
Figure 2. Measuring Circuit

Figure 3. Application Circuit



TYPICAL CHARACTERISTIC CURVES

TYPICAL CHARACTERISTIC CURVES – 8.5 V Version



TYPICAL CHARACTERISTIC CURVES – 8.5 V Version

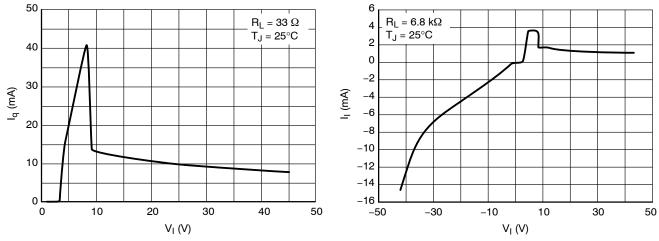
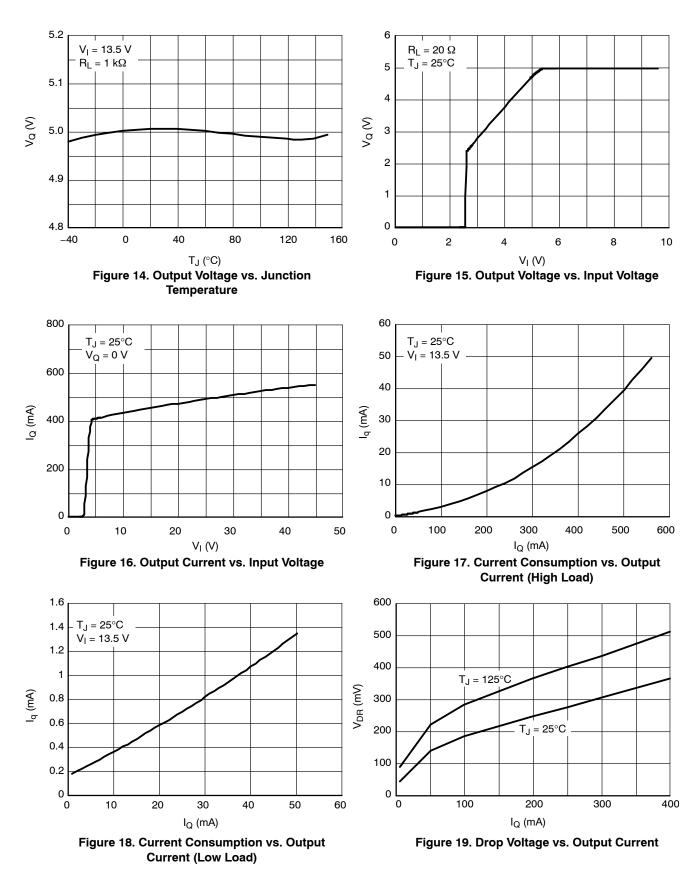


Figure 12. Current Consumption vs. Input Voltage

Figure 13. Input Current vs. Input Voltage

TYPICAL CHARACTERISTIC CURVES – 5.0 V Version



TYPICAL CHARACTERISTIC CURVES – 5.0 V Version

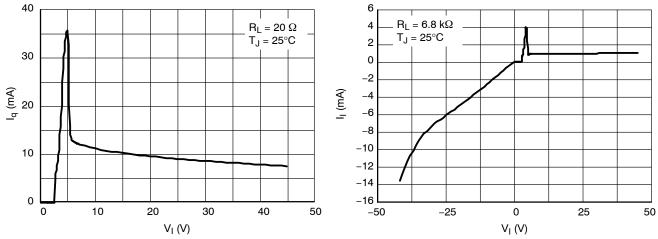
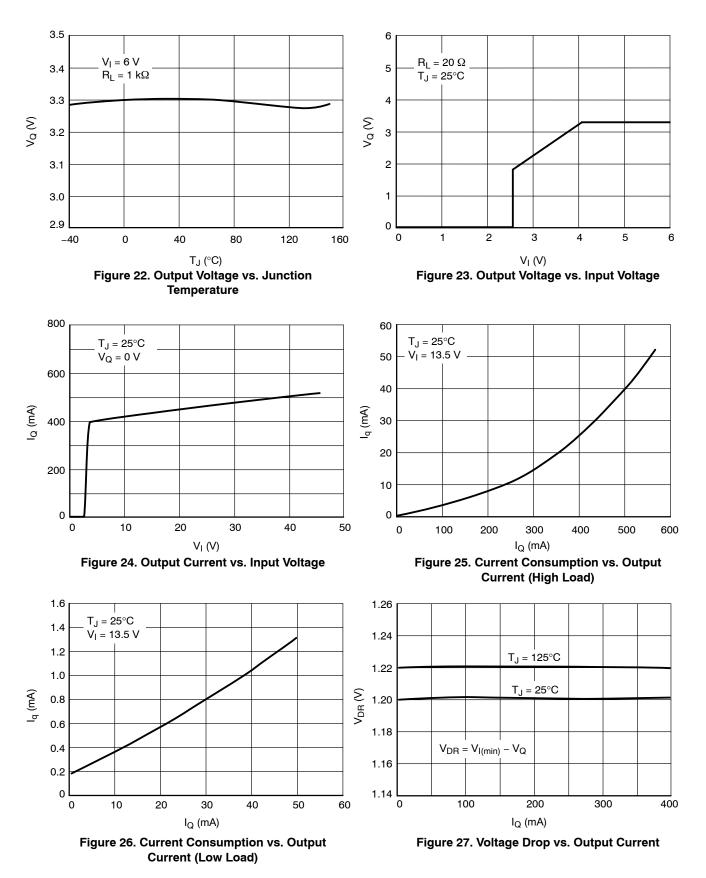


Figure 20. Current Consumption vs. Input Voltage

Figure 21. Input Current vs. Input Voltage

TYPICAL CHARACTERISTIC CURVES – 3.3 V Version



TYPICAL CHARACTERISTIC CURVES – 3.3 V Version

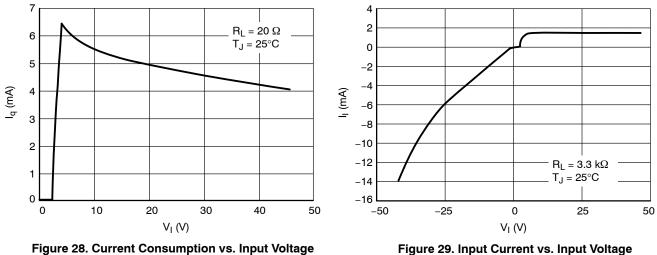
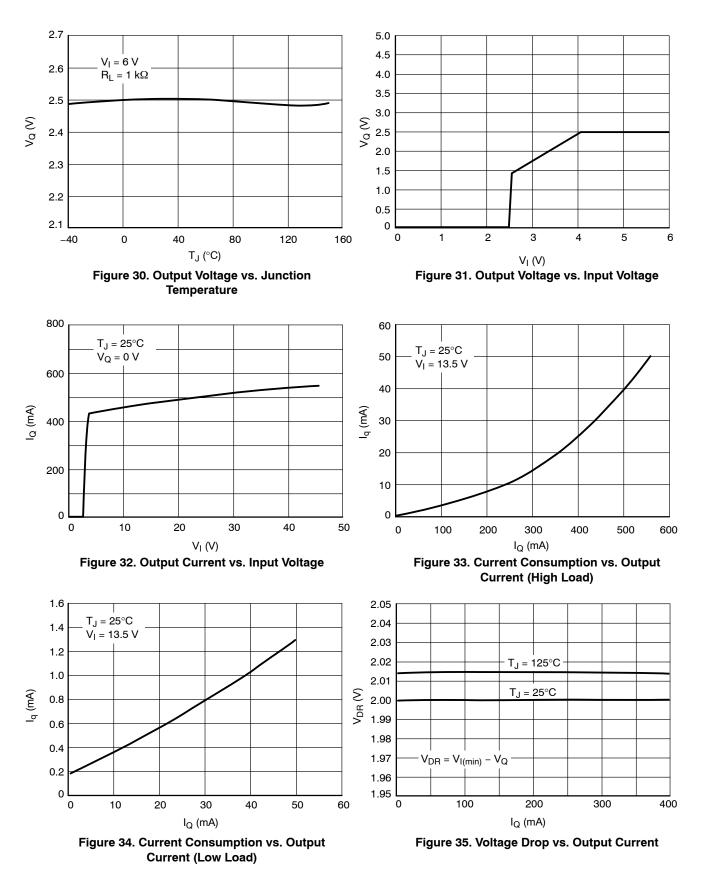


Figure 29. Input Current vs. Input Voltage

TYPICAL CHARACTERISTIC CURVES – 2.5 V Version



TYPICAL CHARACTERISTIC CURVES – 2.5 V Version

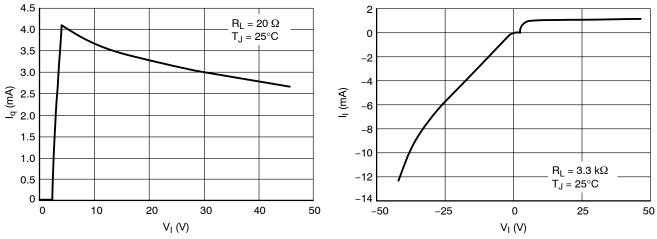


Figure 36. Current Consumption vs. Input Voltage

Figure 37. Input Current vs. Input Voltage

APPLICATION DESCRIPTION

Output Regulator

The output is controlled by a precision trimmed reference and error amplifier. The PNP output has saturation control for regulation while the input voltage is low, preventing over saturation. Current limit and voltage monitors complement the regulator design to give safe operating signals to the processor and control circuits.

Stability Considerations

The input capacitor C_{I1} in Figure 2 is necessary for compensating input line reactance. Possible oscillations caused by input inductance and input capacitance can be damped by using a resistor of approximately 1 Ω in series with C_{I2} .

The output or compensation capacitor helps determine three main characteristics of a linear regulator: startup delay, load transient response and loop stability.

The capacitor value and type should be based on cost, availability, size and temperature constraints. The aluminum electrolytic capacitor is the least expensive solution, but, if the circuit operates at low temperatures (-25° C to -40° C), both the value and ESR of the capacitor will vary considerably. The capacitor manufacturer's data sheet usually provides this information.

The value for the output capacitor C_Q shown in Figure 2 should work for most applications; however, it is not necessarily the optimized solution. Stability is guaranteed at values $C_Q \ge 2.2 \ \mu\text{F}$ and an ESR $\le 2.5 \ \Omega$ within the operating temperature range. Actual limits are shown in a graph in the Typical Performance Characteristics section.

Calculating Power Dissipation in a Single Output Linear Regulator

The maximum power dissipation for a single output regulator (Figure 3) is:

$$P_{D(max)} = [V_{I(max)} - V_{Q(min)}]I_{Q(max)} + V_{I(max)}I_{q}$$
 (eq. 1)

Where:

 $V_{I(max)}$ is the maximum input voltage,

V_{Q(min)} is the minimum output voltage,

 $I_{Q\left(max\right)}$ is the maximum output current for the application, and

 I_q is the quiescent current the regulator consumes at $I_{Q(max)}$.

Once the value of $P_{D(max)}$ is known, the maximum permissible value of R_{0JA} can be calculated:

$$\mathsf{P}_{\theta_{\mathsf{JA}}} = \frac{(150 \text{ C} - \mathsf{T}_{\mathsf{A}})}{\mathsf{P}_{\mathsf{D}}} \tag{eq. 2}$$

The value of $R_{\theta JA}$ can then be compared with those in the package section of the data sheet. Those packages with $R_{\theta JA}$'s less than the calculated value in Equation 2 will keep the die temperature below 150°C. In some cases, none of the packages will be sufficient to dissipate the heat generated by the IC, and an external heat sink will be required. The current flow and voltages are shown in the Measurement Circuit Diagram.

Heat Sinks

A heat sink effectively increases the surface area of the package to improve the flow of heat away from the IC and into the surrounding air.

Each material in the heat flow path between the IC and the outside environment will have a thermal resistance. Like series electrical resistances, these resistances are summed to determine the value of $R_{\theta JA}$:

$$\mathbf{R}_{\theta \mathsf{JA}} = \mathbf{R}_{\theta \mathsf{JC}} + \mathbf{R}_{\theta \mathsf{CS}} + \mathbf{R}_{\theta \mathsf{SA}} \tag{eq. 3}$$

Where:

 $R_{\theta JC}$ = the junction-to-case thermal resistance, $R_{\theta CS}$ = the case-to-heat sink thermal resistance, and $R_{\theta SA}$ = the heat sink-to-ambient thermal resistance. $R_{\theta IC}$ appears in the package section of the data sheet.

Like $R_{\theta JA}$, it too is a function of package type. $R_{\theta CS}$ and $R_{\theta SA}$ are functions of the package type, heat sink and the interface between them. These values appear in data sheets of heat sink manufacturers. Thermal, mounting, and heat sinking are discussed in the ON Semiconductor application note AN1040/D, available on the ON Semiconductor Website.

ORDERING INFORMATION4

Device*	Output Voltage Accuracy	Output Voltage	Package	Shipping †
NCV4274ADS85R4G	2%	8.5 V	D2PAK (Pb–Free)	800 / Tape & Reel
NCV4274DS50G	4%	5.0 V	D2PAK (Pb-Free)	50 Units / Rail
NCV4274DS50R4G	4%	5.0 V	D2PAK (Pb–Free)	800 / Tape & Reel
NCV4274DT50RKG	4%	5.0 V	DPAK (Pb–Free)	2500 / Tape & Reel
NCV4274ADS50G	2%	5.0 V	D2PAK (Pb–Free)	50 Units / Rail
NCV4274ADS50R4G	2%	5.0 V	D2PAK (Pb–Free)	800 / Tape & Reel
NCV4274ADT50RKG	2%	5.0 V	DPAK (Pb–Free)	2500 / Tape & Reel
NCV4274ST33T3G	4%	3.3 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4274DT33RKG	4%	3.3 V	DPAK (Pb–Free)	2500 / Tape & Reel
NCV4274AST33T3G	2%	3.3 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4274ADT33RKG	2%	3.3 V	DPAK (Pb–Free)	2500 / Tape & Reel
NCV4274ADS33R4G	2%	3.3 V	D2PAK (Pb–Free)	800 / Tape & Reel
NCV4274ST25T3G	4%	2.5 V	SOT-223 (Pb-Free)	4000 / Tape & Reel
NCV4274AST25T3G	2%	2.5 V	SOT-223 (Pb-Free)	4000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP

Capable.

DATE 02 OCT 2018

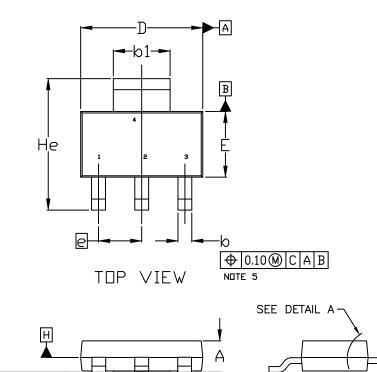




SCALE 1:1

0.10 C

A1



-11

SIDE VIEW

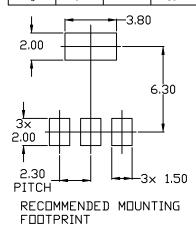
DETAIL A

NDTES:

SOT-223 (TO-261) CASE 318E-04 ISSUE R

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST PDINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS				
DIM	MIN.	NDM.	MAX.		
A	1.50	1.63	1.75		
A1	0.02	0.06	0.10		
b	0.60	0.75	0.89		
b1	2.90	3.06	3.20		
с	0.24	0.29	0.35		
D	6.30	6.50	6.70		
E	3.30	3.50	3.70		
e		2.30 BSC	;		
L	0.20				
L1	1.50	1.75	2.00		
He	6.70	7.00	7.30		
θ	0*		10*		



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SOT-223 (TO-261) CASE 318E-04 ISSUE R

DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	Style 9: Pin 1. Input 2. Ground 3. Logic 4. Ground	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	Style 12: Pin 1. Input 2. Output 3. NC 4. Output	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*

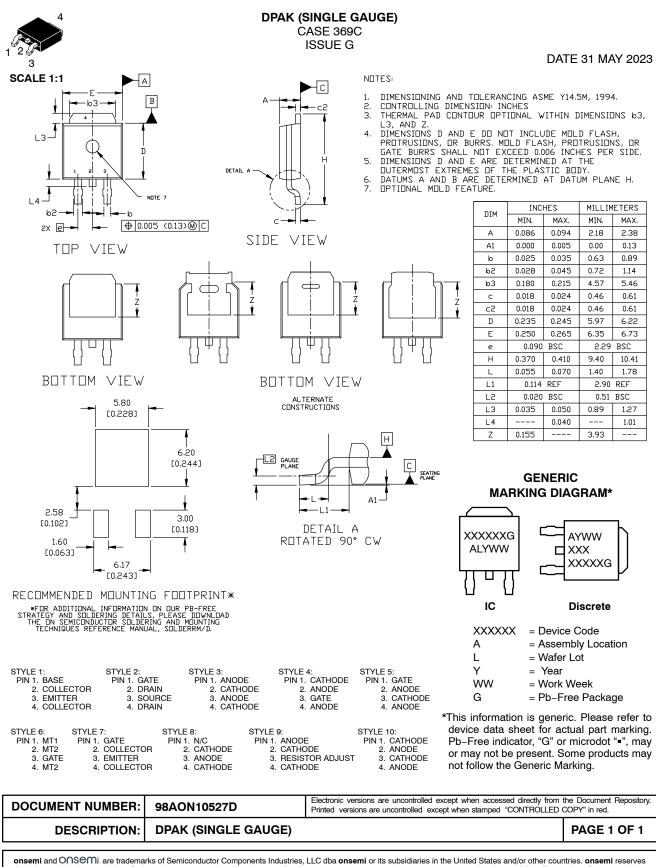


- A = Assembly Location
- Y = Year
- W = Work Week
- XXXXX = Specific Device Code
- = Pb-Free Package
- (Note: Microdot may be in either location) *This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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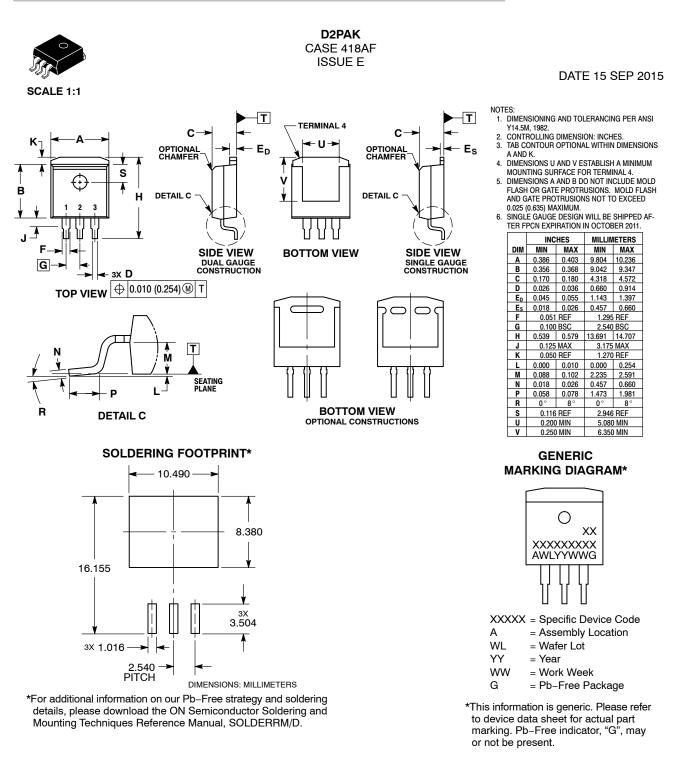
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